



STB270N4F3 STI270N4F3

N-channel 40 V, 1.6 mΩ, 160 A, D²PAK, I²PAK
STripFET™ III Power MOSFET

Features

Type	V _{DSS}	R _{DS(on) max}	I _D	P _{TOT}
STB270N4F3	40 V	< 2.0 mΩ	160 A	330 W
STI270N4F3	40 V	< 2.6 mΩ	120 A	330 W

- 100% avalanche tested
- Standard threshold drive

Applications

- High current, switching application
 - Automotive

Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performances.

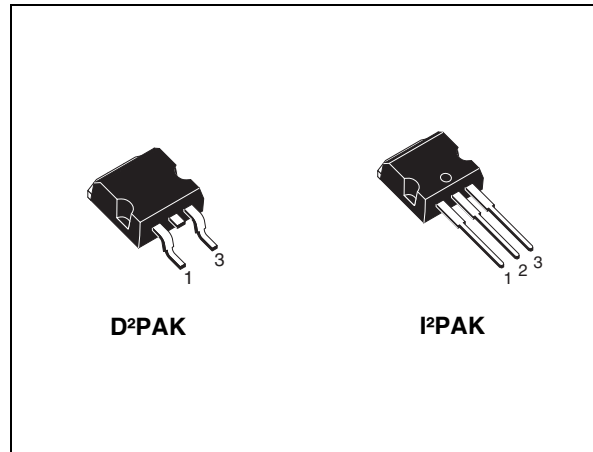


Figure 1. Internal schematic diagram

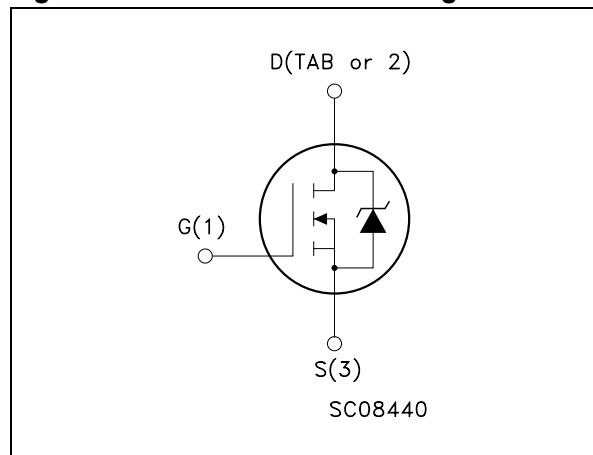


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB270N4F3	270N4F3	D ² PAK	Tape and reel
STI270N4F3	270N4F3	I ² PAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		I ² PAK	D ² PAK	
V _{DS}	Drain-source voltage (V _{GS} = 0)	40		V
V _{GS}	Gate-source voltage	± 20		V
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25 °C	120	160	A
I _D ⁽¹⁾	Drain current (continuous) at T _C =100 °C	120	160	A
I _{DM} ⁽²⁾	Drain current (pulsed)	480	640	A
P _{TOT}	Total dissipation at T _C = 25 °C	330		W
	Derating factor	2.2		W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	3.5		V/n
E _{AS} ⁽⁴⁾	Single pulse avalanche energy	1		J
T _J T _{stg}	Operating junction temperature Storage temperature	-55 to 175		°C

1. Current limited by package
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 120 A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ T_{JMAX}
4. Starting T_J=25 °C, I_D =80 A, V_{DD}= 32 V

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		I ² PAK	D ² PAK	
R _{thj-case}	Thermal resistance junction-case max	0.45		°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max		35	°C/W
R _{thj-a}	Thermal resistance junction-ambient max	62.5		°C/W
T _I	Maximum lead temperature for soldering purpose (for 10 sec, 1.6 mm from case)	300		°C

1. When mounted on 1inch² FR-4 board, 2 oz Cu.

2 Electrical characteristics

($T_{CASE}=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	40			V	
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating}$ @125 °C			10	μA	
					100	μA	
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 200	nA	
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V	
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 80\text{ A}$	I ² PAK		2.1	2.6	m Ω
			D ² PAK		1.6	2.0	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$, $I_D = 80\text{ A}$	-	200		S
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	7400		pF
C_{oss}	Output capacitance			1800		pF
C_{rss}	Reverse transfer capacitance			47		pF
Q_g	Total gate charge	$V_{DD} = 20\text{ V}$, $I_D = 160\text{ A}$	-	110	150	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$		27		nC
Q_{gd}	gate-drain charge	(see Figure 14)		25		nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 80\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	22	-	ns
	Rise time			180	-	ns
$t_{d(off)}$ t_f	Turn-off delay time	$V_{DD} = 20\text{ V}$, $I_D = 80\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	110	-	ns
	Fall time			45	-	ns

Table 7. Source drain diode

Symbol	Parameter		Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current	D ² PAK		-		160	A
		I ² PAK		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)	D ² PAK		-		640	A
		I ² PAK		-		480	A
$V_{SD}^{(2)}$	Forward on voltage		$I_{SD}=80\text{ A}, V_{GS}=0$	-		1.5	V
t_{rr}	Reverse recovery time		$I_{SD}=160\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s},$ $V_{DD}=32\text{ V}, T_j=150\text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	70		ns
Q_{rr}	Reverse recovery charge	nC					
I_{RRM}	Reverse recovery current	A					

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

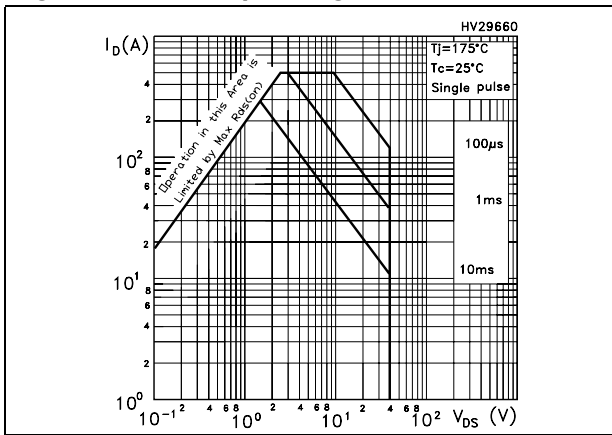


Figure 3. Thermal impedance

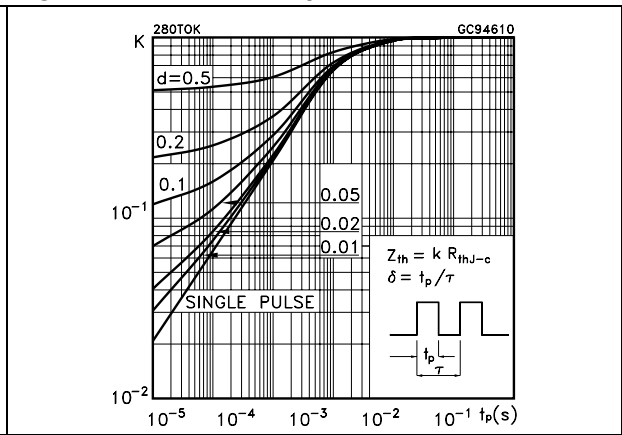


Figure 4. Output characteristics

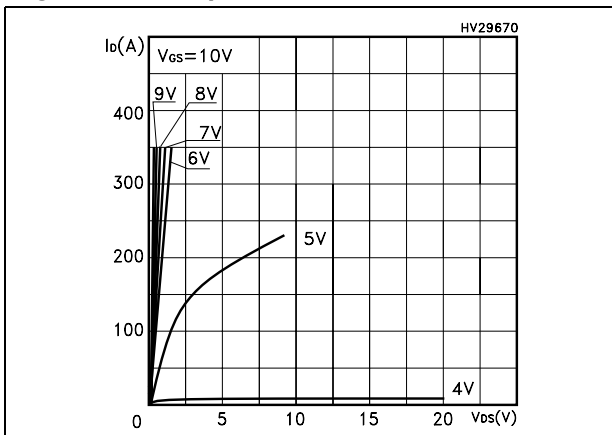


Figure 5. Transfer characteristics

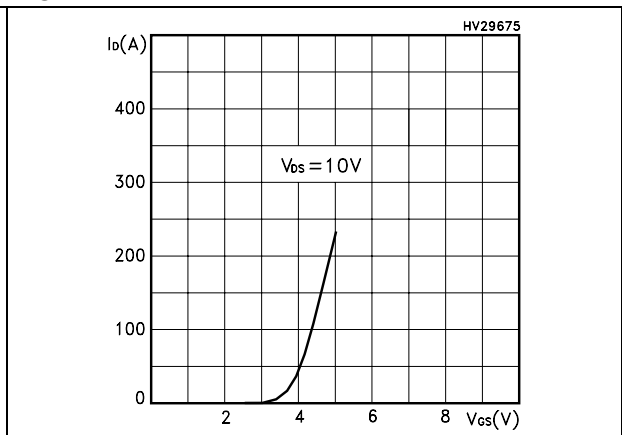


Figure 6. Static drain-source on resistance

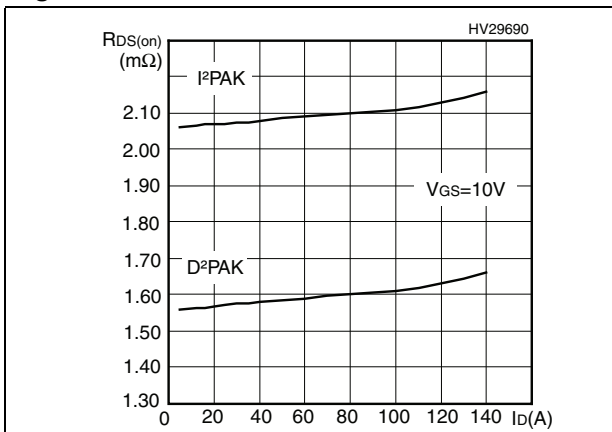


Figure 7. Normalized $B_{V_{DS}}$ vs temperature

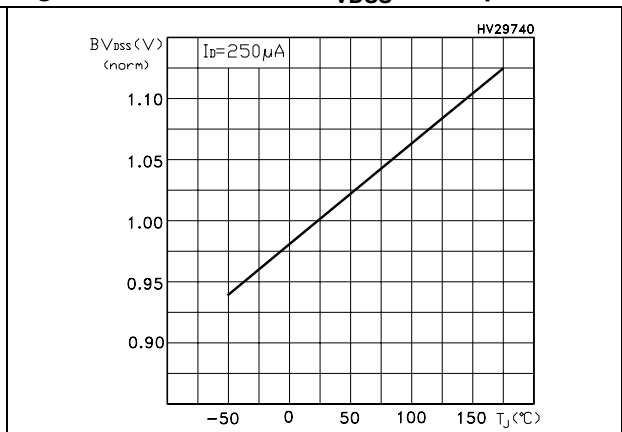


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

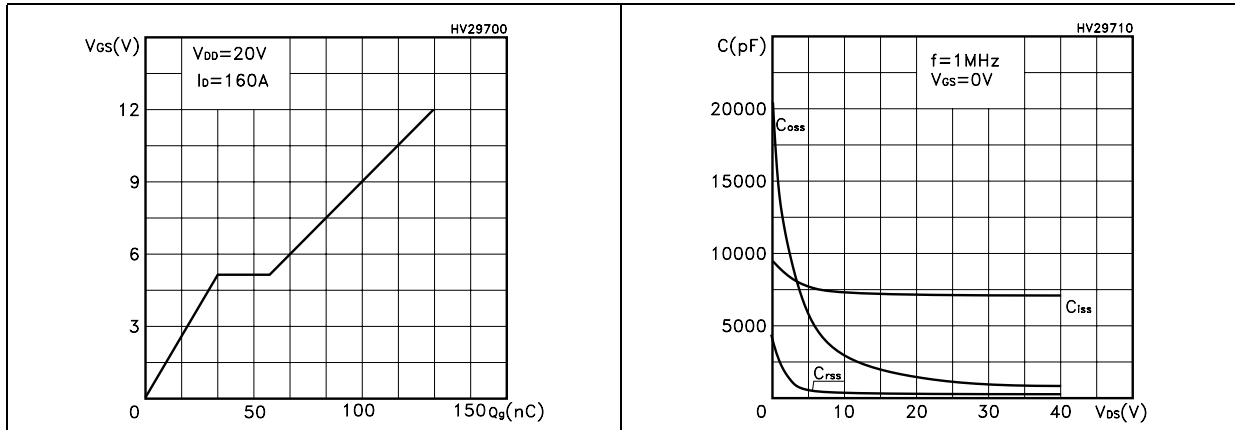


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

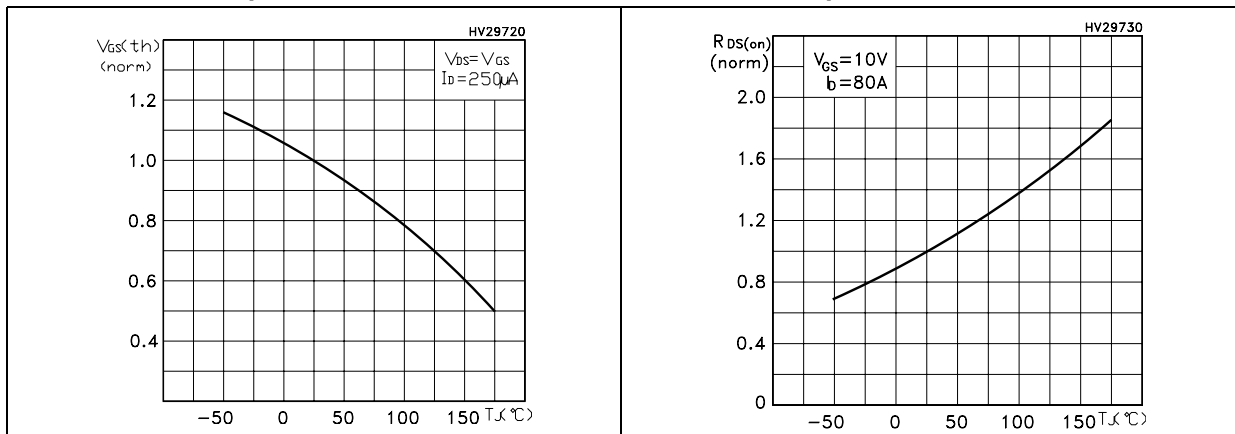
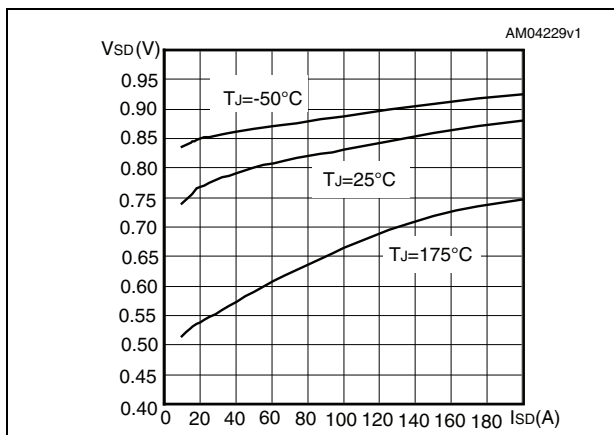


Figure 12. Source-drain diode forward characteristics



3 Test circuit

Figure 13. Switching times test circuit for resistive load

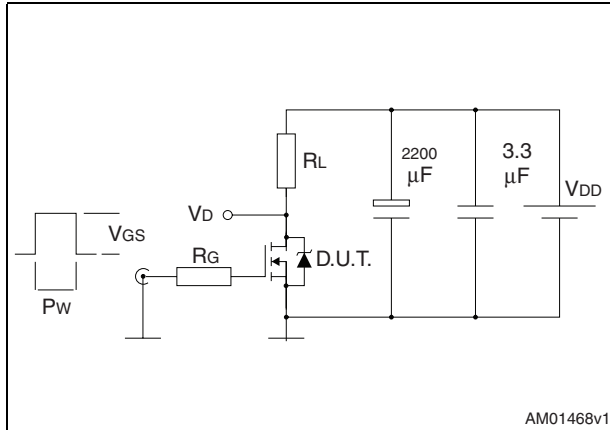


Figure 14. Gate charge test circuit

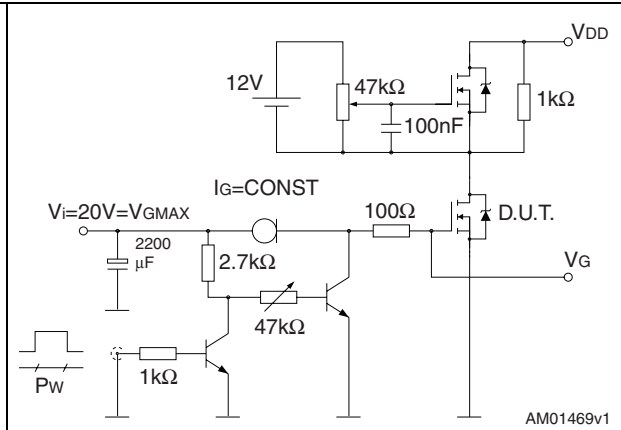


Figure 15. Test circuit for inductive load switching and diode recovery times

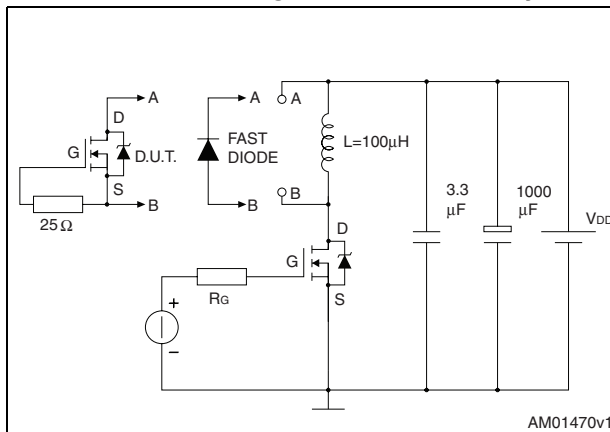


Figure 16. Unclamped inductive load test circuit

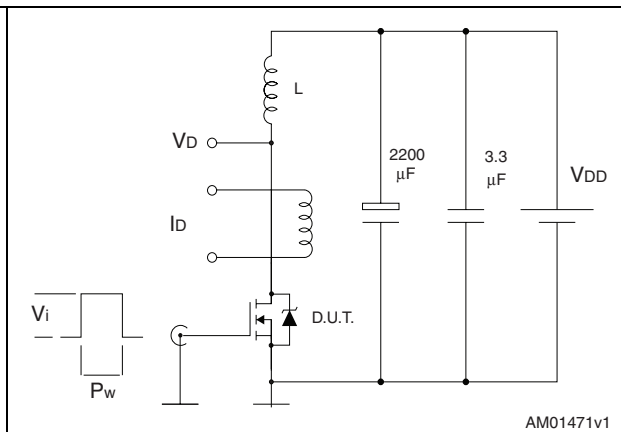


Figure 17. Unclamped inductive waveform

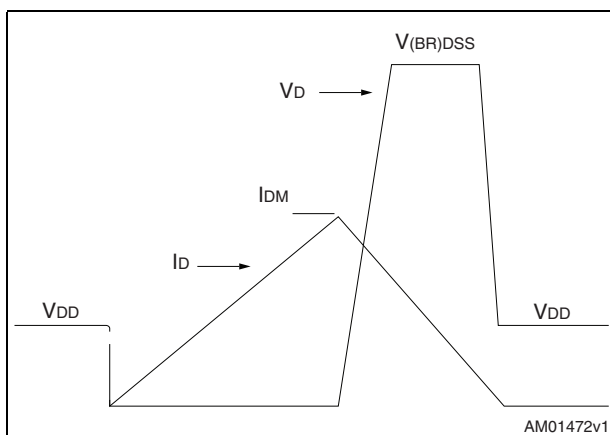
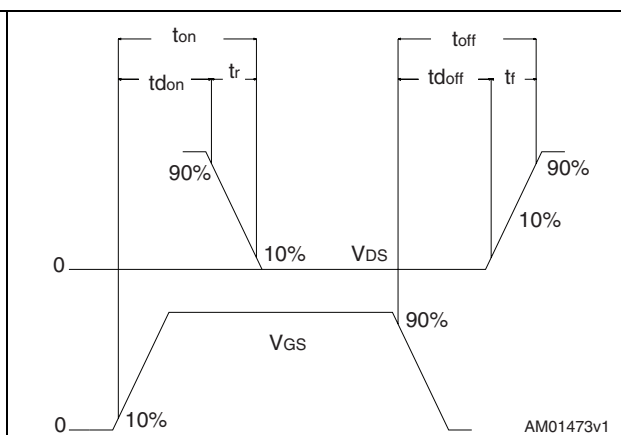


Figure 18. Switching time waveform

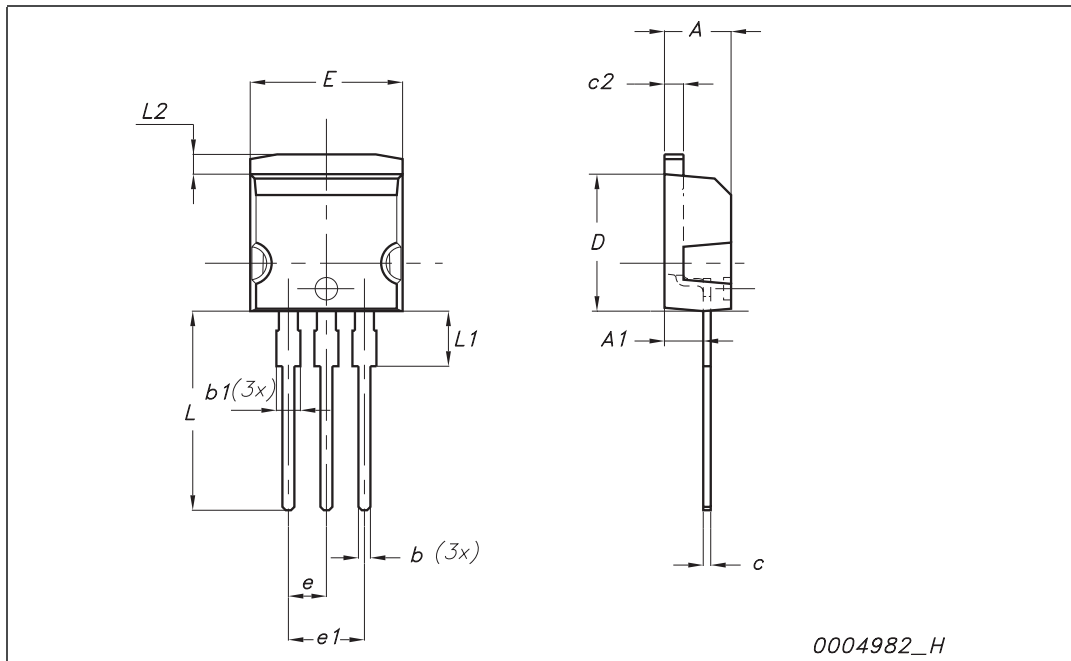


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

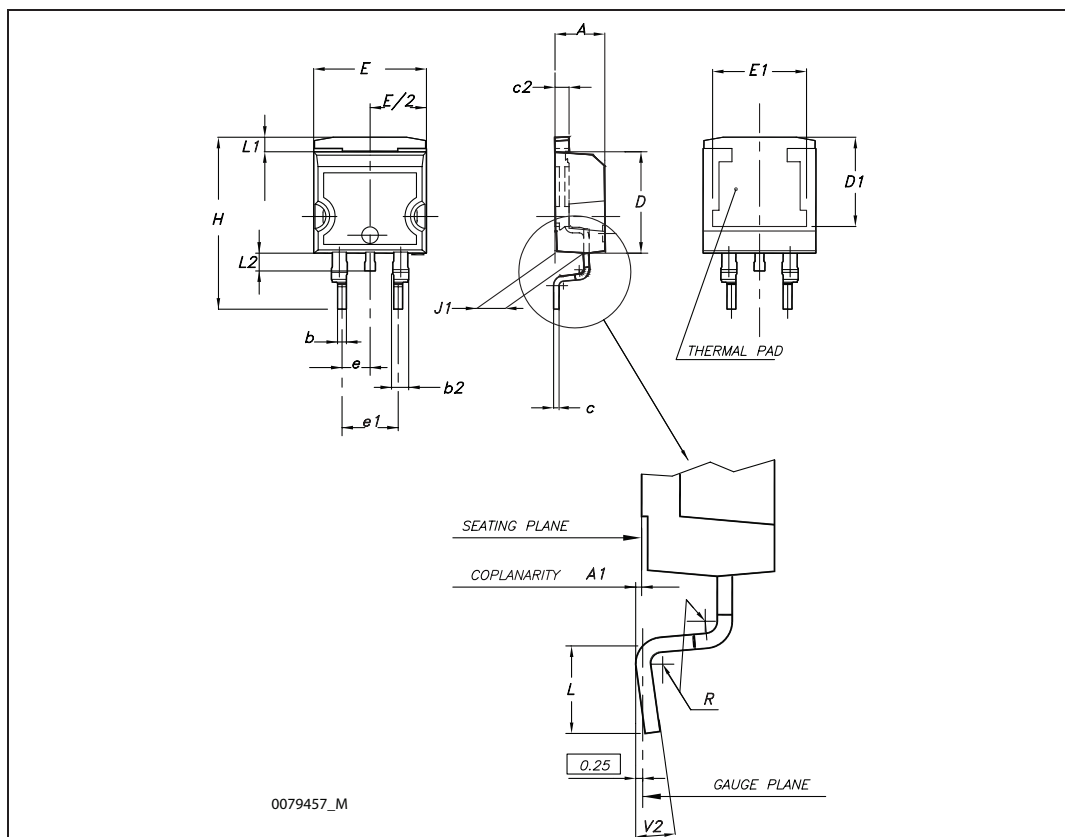
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



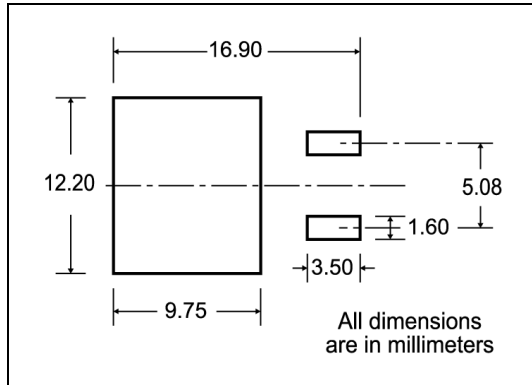
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION

Bending radius R min.

* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
07-Feb-2007	1	Initial release.
02-Apr-2008	2	Some value changes on Table 2
06-May-2009	3	Changed: Description and Figure 12: Source-drain diode forward characteristics
14-Jul-2009	4	Removed package and mechanical data: TO-220

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